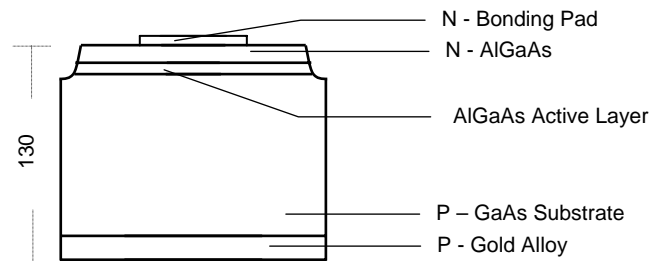
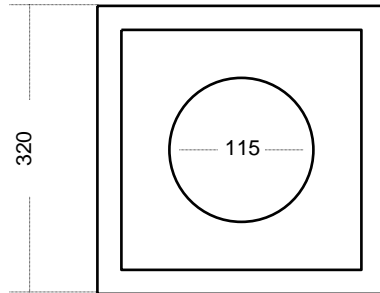


TCD850-900-3

❖ Outline Dimensions:

Unit: μm



❖ Physical Structure:

Chip dimensions	Chip size	12 mil x 12 mil	320 μm x 320 μm
	Thickness	5.1 mil	130 μm
	Bonding pad	4.5 mil	115 μm

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	-	-	1.6	V
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	5	-	-	V
Peak Wavelength	λ_P	$I_F = 20\text{mA}$	850	-	900	nm
Output Power	P_O	$I_F = 20\text{mA}$	4.3	-	-	mW